

SANYO

No.3823

2SK1728

N-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

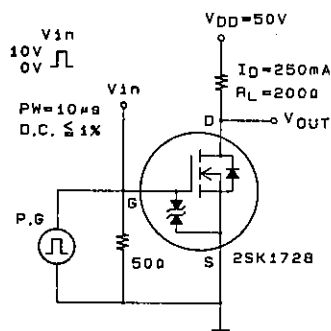
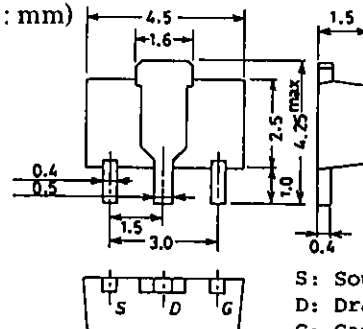
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DS}	100	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	1	A
Drain Current(Pulse)	I_{DP}	4	A
Allowable Power Dissipation	P_D	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$ $T_c = 25^\circ\text{C}$ Mounted on ceramic board ($250\text{mm}^2 \times 0.8\text{mm}$)	3.5 1.3 W W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DS}$	$I_D = 1\text{mA}, V_{GS} = 0$	100			V
Zero Gate Voltage	I_{DSS}	$V_{DS} = 100\text{V}, V_{GS} = 0$			100	μA
Drain Current						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	1.0		2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 500\text{mA}$	0.6	1.0		S
Static Drain to Source	$R_{DS(on)}$	$I_D = 500\text{mA}, V_{GS} = 10\text{V}$		2.7	3.5	Ω
on State Resistance	$R_{DS(on)}$	$I_D = 500\text{mA}, V_{GS} = 4\text{V}$		3.2	4.2	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		45		pF
Output Capacitance	C_{oss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		15		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		3		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		5		ns
Rise Time	t_r	"		10		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		30		ns
Fall Time	t_f	"		20		ns
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0$		1.0		V

Switching Time Test Circuit**Package Dimensions 2062**
(unit : mm)

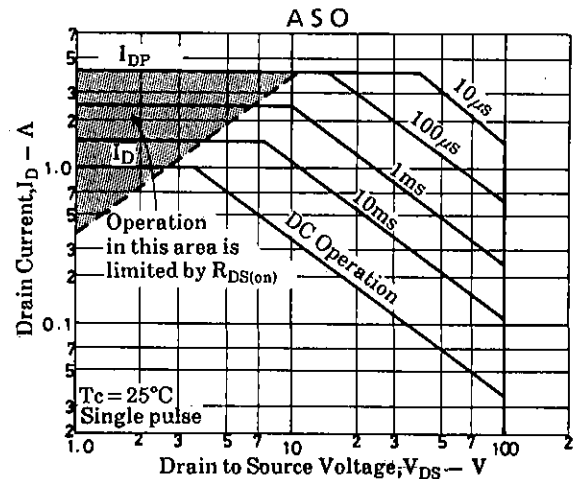
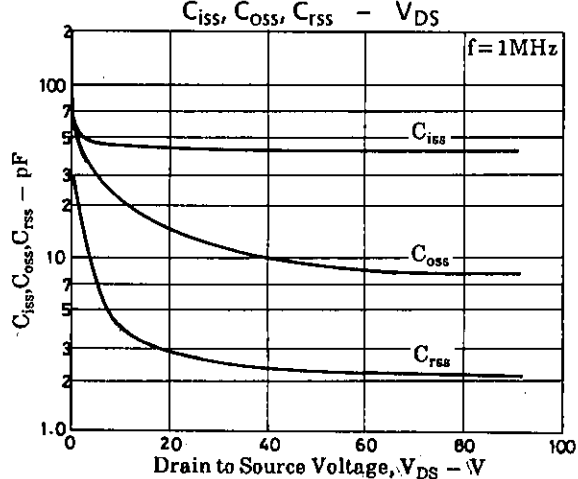
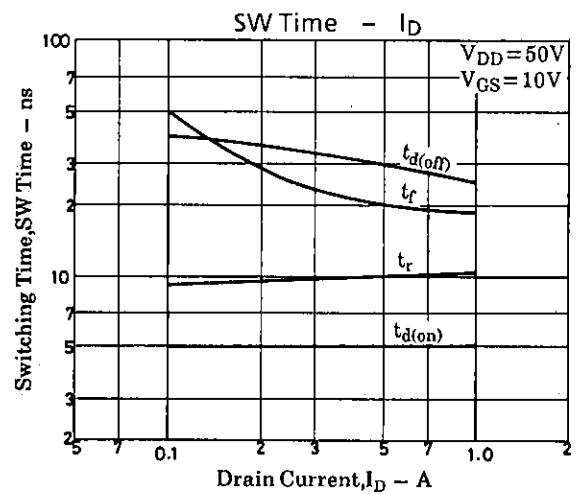
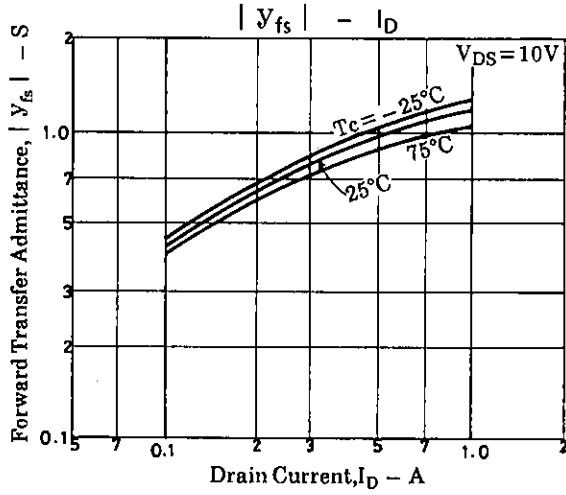
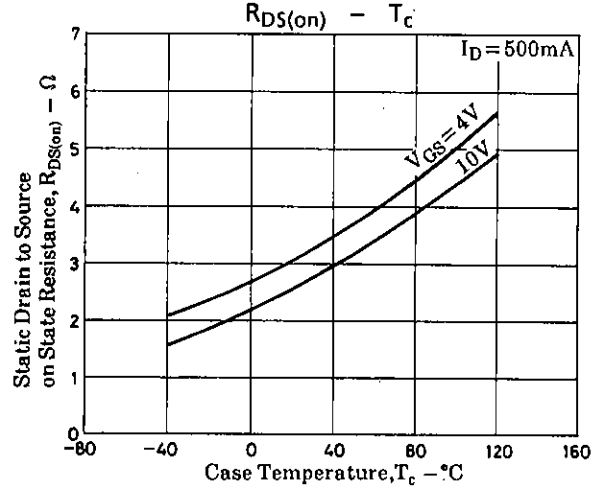
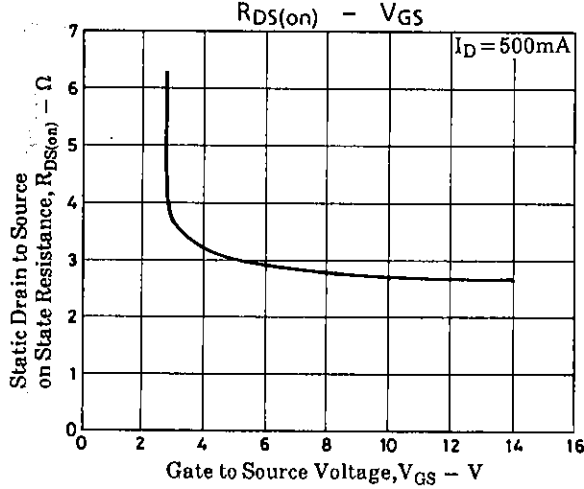
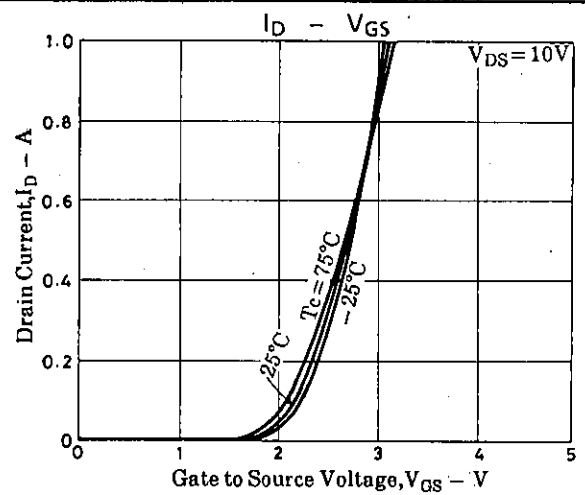
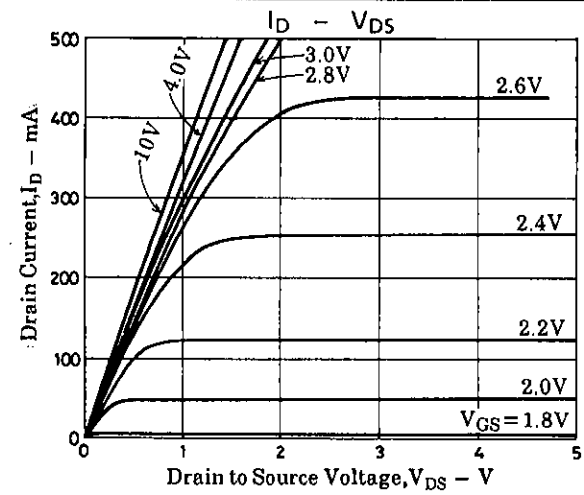
S: Source
D: Drain
G: Gate

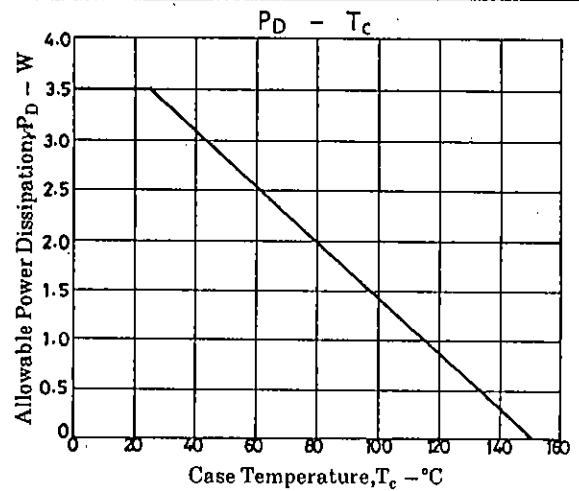
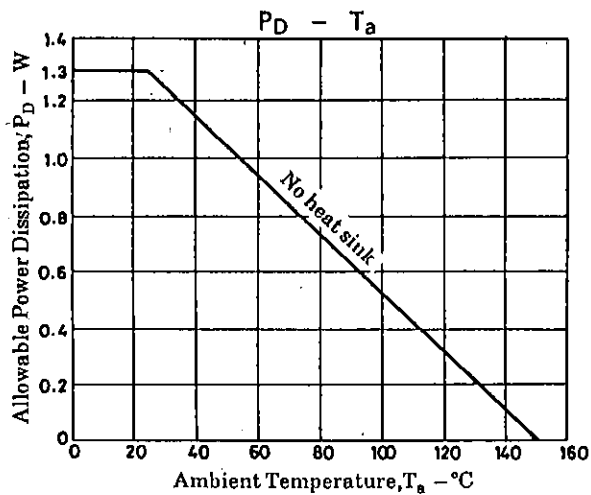
SANYO: PCP

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

32593TH (KOTO) 8-7833 No.3823-1/3





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.